

2SD1575

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

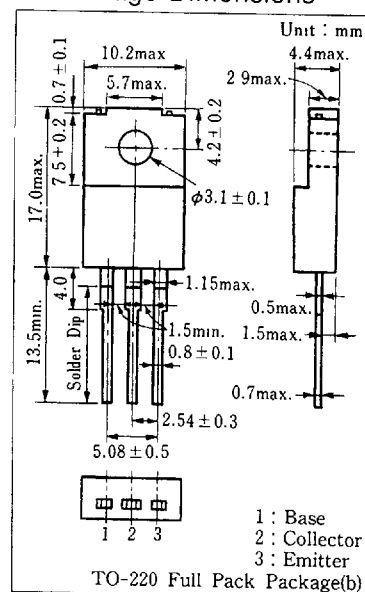
■ Features

- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	1500	V
Collector-emitter voltage	V_{CES}	1500	V
	V_{CEO}	700	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Peak collector current	I_{CP}	6	A
Peak base current	I_{BP}	2.5	A
Reverse peak base current	I_{BP}	-1.5	A
Collector power dissipation	Tc = 25 °C	40	W
	Ta = 25 °C	2.0	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

■ Package Dimensions



■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CE}=750\text{ V}, I_E=0$			50	μA
		$V_{CB}=1500\text{ V}, I_E=0$			1	mA
Emitter-base voltage	V_{EBO}	$I_E=1\text{ mA}, I_C=0$	6			V
DC current gain	h_{FE}	$V_{CE}=5\text{ V}, I_C=2\text{ A}$	2		5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=1\text{ A}$			5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}, I_B=1\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{ V}, I_C=0.5\text{ A}, f=0.5\text{ MHz}$		2		MHz
Fall time	t_f	$I_C=2.5\text{ A}, I_{Bend}=1.1\text{ A}$			1	μs
Storage time	t_{stg}	$L_B=10\text{ }\mu\text{H}$			9	μs

